

AMENDMENTS TO THE SPECIFICATION

Please amend the specification of the instant application by inserting the following paragraph between paragraphs [0039] and [0040]:

[0039.1] A monolithic three dimensional memory array is one in which multiple memory levels are formed above a single substrate, such as a wafer, with no intervening substrates. In contrast, stacked memories have been constructed by forming memory levels on separate substrates and adhering the memory levels atop each other, as in Leedy, US Patent No. 5,915,167, "Three dimensional structure memory." The substrates may be thinned or removed from the memory levels before bonding, but as the memory levels are initially formed over separate substrates, such memories are not true monolithic three dimensional memory arrays.

This paragraph appears as paragraph [0061] of Petti et al., US Patent Application No. 10/728,230, "Semiconductor Device Including Junction Diode Contacting Contact-Antifuse Unit Comprising Silicide," now US Patent No. 6,946,719, which is incorporated by reference in paragraph [0002] of the instant application. As addition of this paragraph merely restates material previously incorporated by reference, this specification amendment does not constitute new matter.